

STATUS OF CLAIMS

Claims 1-27 are pending.

PLEASE AMEND THE CLAIMS AS FOLLOWS:

4. (AMENDED) The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an [an oxygen containing plasma etchable material selected from the group consisting of oxygen containing plasma etchable conductor materials, oxygen containing plasma etchable semiconductor materials, and] oxygen containing plasma etchable dielectric material[s].

Add claims 17-27 as follows:

17. The method of Claim 4 wherein said oxygen containing plasma etchable dielectric material is a low dielectric constant material.

18. The method of Claim 17 wherein said low dielectric constant material is a polyimide organic polymer spin-on polymer dielectric material.

19. The method of Claim 17 wherein said low dielectric constant material is a spin-on low dielectric constant material.

20. The method of Claim ¹⁹ wherein said spin-on low dielectric constant material is a poly (arylene ether) organic polymer spin-on polymer dielectric material.

21. The method of Claim ¹⁹ wherein said spin-on low dielectric constant material is a fluorinated poly (arylene ether) organic polymer spin-on polymer dielectric material.

22. The method of Claim ¹⁷ wherein said low dielectric constant material is an amorphous carbon dielectric material.

23. The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an oxygen containing plasma etchable conductor material.

24. The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an oxygen containing plasma etchable semiconductor material.

25. The method of Claim 19 wherein said spin-on low dielectric constant material is a hydrogen silsesquioxane spin-on-glass dielectric material.

26. The method of Claim 19 wherein said spin-on low dielectric constant material is a carbon bonded hydrogen silsesquioxane spin-on-glass dielectric material.

27. The method of Claim 19 wherein said spin-on low dielectric constant material is a carbon bonded fluorocarbon silsesquioxane spin-on-glass dielectric material.

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1. The method of Claim 19 wherein said spin-on low dielectric constant material is a carbon bonded fluorocarbon silsesquioxane spin-on-glass dielectric material.